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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/995,031	11/29/2001	Ricky Amos	YOR920010633US1	9669		
23389	7590 11/29/2005		EXAMINER			
SCULLY SCOTT MURPHY & PRESSER, PC			LANDAU, M	LANDAU, MATTHEW C		
400 GARDEN CITY PLAZA			1001010	DARED MINIDED		
SUITE 300			ART UNIT	PAPER NUMBER		
GARDEN CITY, NY 11530			2815			

DATE MAILED: 11/29/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)	_		
		09/995,031	AMOS ET AL.			
	Office Action Summary	Examiner	Art Unit	_		
		Matthew Landau	2815			
Period fo	The MAILING DATE of this communication app or Reply	ears on the cover sheet with the c	orrespondence address			
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY CHEVER IS LONGER, FROM THE MAILING DANSIONS of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. period for reply is specified above, the maximum statutory period we are to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 16(a). In no event, however, may a reply be tin iill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D. (35 U.S.C. § 133).			
Status						
1)⊠	Responsive to communication(s) filed on 17 No	ovember 2005.				
3)	- · · · · · · · · · · · · · · · · · · ·					
,—	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Dispositi	ion of Claims					
4\⊠	Claim(s) <u>1,2,4,5,7-11 and 13-16</u> is/are pending	in the application				
•	4a) Of the above claim(s) is/are withdraw	• •				
	Claim(s) is/are allowed.	m nom consideration.				
·	Claim(s) <u>1,2,4,5,7-11 and 13-16</u> is/are rejected					
7)	Claim(s) is/are objected to.	•				
·—	Claim(s) are subject to restriction and/or	election requirement				
,—		election requirement.				
Applicati	on Papers					
9)[The specification is objected to by the Examiner	•				
10)	The drawing(s) filed on is/are: a)□ acce	epted or b) \square objected to by the ${ t I}$	Examiner.			
	Applicant may not request that any objection to the o	drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).			
	Replacement drawing sheet(s) including the correcti	on is required if the drawing(s) is obj	ected to. See 37 CFR 1.121(d).			
11)	The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form PTO-152.			
Priority ເ	ınder 35 U.S.C. § 119					
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
2) 🔲 Notice 3) 🔯 Inform	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) No(s)/Mail Date 7/11/2003	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:				

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DETAILED ACTION

Response to Amendment

The declaration filed on November 1, 2005 under 37 CFR 1.131 is sufficient to overcome the Brown et al. reference (US Pat. 6,541,320).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1, 2, 5, 7-11, and 14-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Talwar et al. (US Pat. 6,300,208, hereinafter Talwar).

Regarding claims 1, 2, 5, 7-11, and 14-16, Figure 2H of Talwar discloses a MOSFET comprising: a semi-conducting substrate 4 (n or p-type silicon) (col. 4, lines 39-41 and col. 5, lines 6-10) having source and drain regions (5 and 6); a gate dielectric layer 8 made of SiO₂ (col. 5, lines 14-16); and a gate 9 formed of Re (col. 5, lines 46-50). The difference between Talwar and the claimed invention is the gate dielectric has a thickness of less than 50 angstroms. However, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the invention of by, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art. In re Aller, 105 USPQ 233. The ordinary artisan would

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have been motivated to modify in the manner described above for the purpose of increasing the integration density (by forming smaller devices).

Claims 1, 2, 4, 7-11, and 13-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Maria et al. (US PGPub 2001/0032995, hereinafter Maria) in view of Talwar.

Regarding claims 1, 2, 4, 8-11, 13, 15, and 16, Figure 4 of Maria discloses a MOSFET device comprising: a semi-conducting substrate 16 (silicon) having source and drain regions (12 and 14); a gate dielectric layer 20'''(20a/20b) (silicate of La₂O₃) of less than 50 angstroms thickness (see page 3, paragraph [0033]) on said semi-conducting substrate 16; and a gate 22 formed of Pt (see page 3, paragraph [0034]) on top of said dielectric layer 20'''. The difference between Maria and the claimed invention is the gate electrode comprises Re. Figure 2H of Talwar discloses a MOSFET device comprising a gate electrode 9 made of Re or Pt (col. 5, lines 46-50). In view of such teaching, it would have been obvious to the ordinary artisan at the time the invention was made to modify the invention of Maria by using Re as the gate electrode for the purpose of selecting an equivalent material that is known in the art to be used for the same purpose (see MPEP 2144.06).

Regarding claims 7 and 14, Figure 4 of Maria discloses the semi-conducting substrate 16 is n-type or p-type. It is inherent to have a doped substrate (n-type or p-type) in order to create a channel region below the gate.

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Response to Arguments

Applicant's arguments with respect to claims 1 and 10 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew C. Landau whose telephone number is (571) 272-1731.

The examiner can normally be reached from 8:30 AM - 5:30 PM. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone numbers for the organization where this application or proceeding is assigned are (571) 273-8300 for regular communications and (571) 273-8300 for After Final communications.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should any questions arise regarding access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

> SPE Kenneth Parker TCZ800 Matthew C. Landau

November 25, 2005